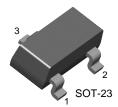


SEMICONDUCTOR®

KST4126

General Purpose Transistor



1. Base 2. Emitter 3. Collector

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_a=25$ °C unless otherwise noted

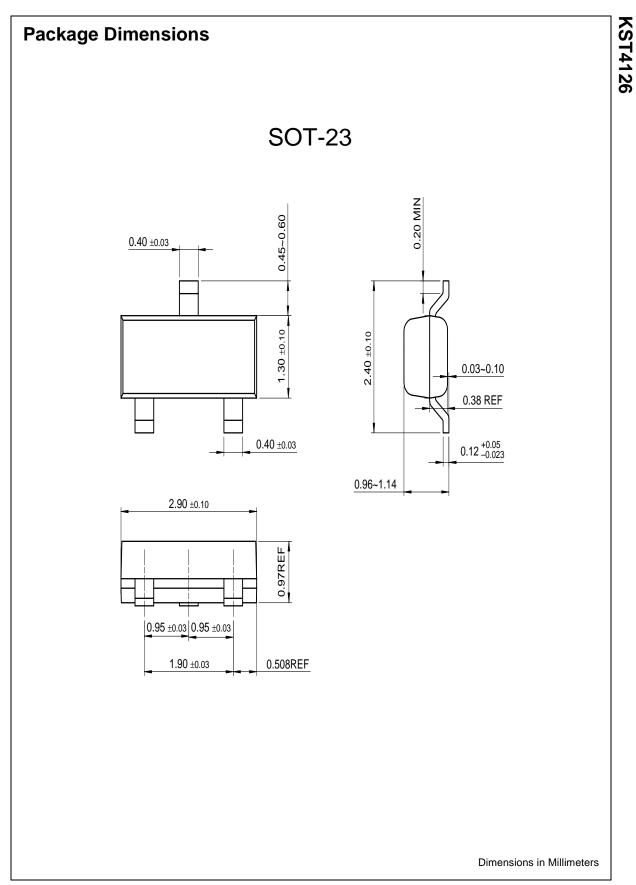
Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-25	V
V _{CEO}	Collector-Emitter Voltage	-25	V
V _{EBO}	Emitter-Base Voltage	-4	V
I _C	Collector Current	-200	mA
P _C	Collector Power Dissipation	350	mW
T _{STG}	Storage Temperature	150	°C
R _{TH} (j-a)	Thermal Resistance junction to Ambient	357	°C/W

Electrical Characteristics $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = -10μA, I _E =0	-25		V
BV _{CEO}	* Collector-Emitter Breakdown Voltage	I _C = -1mA, I _E =0	-25		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = -10μA, I _C =0	-4		
I _{CBO}	Collector Cut-off Current	V _{CB} = -20V, I _E =0		-50	nA
I _{EBO}	Emitter Cut-off Current	V _{BE} = -3V, I _C =0		-50	nA
h _{FE}	* DC Current Gain	V _{CE} = -1V, I _C = -2mA	120	360	
		V_{CE} = -1V, I_{C} = -50mA	60		
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	I _C = -50mA, I _B = -5mA		-0.4	V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	I _C = -50mA, I _B = -5mA		-0.95	V
f _T	Current Gain Bandwidth Product	V _{CE} = -20V, I _C = -10mA, f=100MHz	250		MHz
C _{ib}	Input Capacitance	V _{BE} = -0.5V, I _C =0, f=1MHz		10	pF
C _{ob}	Output Capacitance	V _{CB} = -5V, I _E =0, f=1MHz		4.5	pF
NF	Noise Figure	V_{CE} = -5V, I _C = -100µA, R _S =1KΩ		4	dB
		Noise Bandwidth=10Hz to 15.7KHz			

* Pulse Test: PW≤300µs, Duty Cycle≤2%





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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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